IXYS

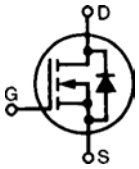
HiPerFET™ Power MOSFETs

	V_{DSS}	I_{D25}	$R_{DS(on)}$
IXFH/~~IXFM~~ 10 N90	900 V	10 A	1.1 Ω
IXFH/~~IXFM~~ 12 N90	900 V	12 A	0.9 Ω
IXFH/IXFT 13 N90	900 V	13 A	0.8 Ω

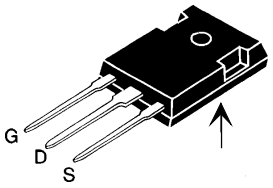
$t_{rr} \leq 250$ ns

N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

Obsolete:
IXFM10N90
IXFM12N90



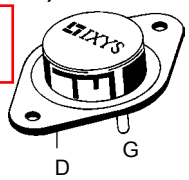
TO-247 AD (IXFH)



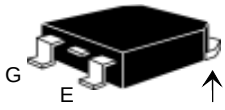
(TAB)

~~**TO-204 AA (IXFM)**~~

Package unavailable



TO-268 (IXFT)



G = Gate, D = Drain,
S = Source, TAB = Drain

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		900	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		900	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C	10N90	10	A
		12N90	12	A
		13N90	13	A
I_{DM}	T_C = 25°C,	10N90	40	A
	pulse width limited by T_{JM}	12N90	48	A
		13N90	52	A
I_{AR}	T_C = 25°C	10N90	10	A
		12N90	12	A
		13N90	13	A
E_{AR}	T_C = 25°C		30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150$°C, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		300	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 3 mA		900			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2.0		4.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$	T_J = 25°C			25	µA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5 \cdot I_{D25}$	10N90			1.1	Ω
		12N90			0.9	Ω
		13N90			0.8	Ω
	Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %					

Features
- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

Applications
- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

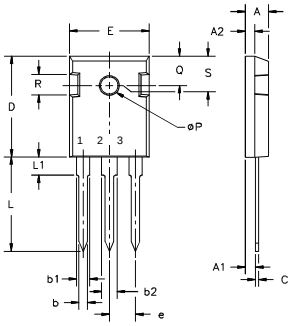
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Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25}, pulse test	6	12		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4200		pF
C_{oss}			315		pF
C_{rss}			90		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}; R_G = 2 Ω (External)		18	50	ns
t_r			12	50	ns
$t_{d(off)}$			51	100	ns
t_f			18	50	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		123	155	nC
Q_{gs}			27	45	nC
Q_{gd}			49	80	nC
R_{thJC}				0.42	K/W
R_{thCK}	(IXFH/IXFM)		0.25		K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		min.	typ.	max.	
I_S	V_{GS} = 0 V	10N90			10	A
		12N90			12	A
		13N90			13	A
I_{SM}	Repetitive; pulse width limited by T_{JM}	10N90			40	A
		12N90			48	A
		13N90			52	A
V_{SD}	$I_F = I_S$, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %				1.5	V
t_{rr}	$I_F = I_S$, -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C			250	ns
		T_J = 125°C			400	ns
Q_{RM}		T_J = 25°C		1		µC
		T_J = 125°C		2		µC
I_{RM}		T_J = 25°C		10		A
		T_J = 125°C		15		A

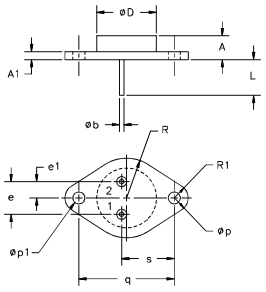
TO-247 AD (IXFH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

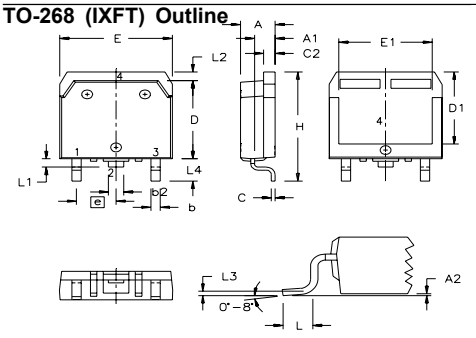
TO-204 AA (IXFM) Outline



Pins 1 - Gate 2 - Source
Case - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	6.4	11.4	.250	.450
A1		3.42		.135
Øb	.97	1.09	.038	.043
ØD		22.22		.875
e	10.67	11.17	.420	.440
e1	5.21	5.71	.205	.225
L	7.93		.312	
Øp	3.84	4.19	.151	.165
Øp1	3.84	4.19	.151	.165
q	30.15 BSC		1.187 BSC	
R		13.33		.525
R1		4.77		.188
s	16.64	17.14	.655	.675

TO-268 (IXFT) Outline



SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig. 1. Output Characteristics

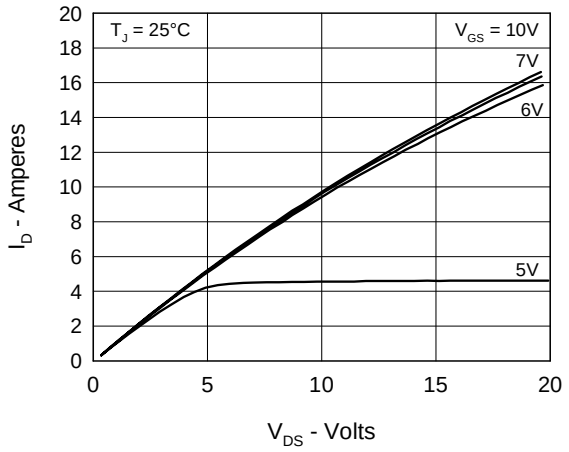


Fig. 2. Input Admittance

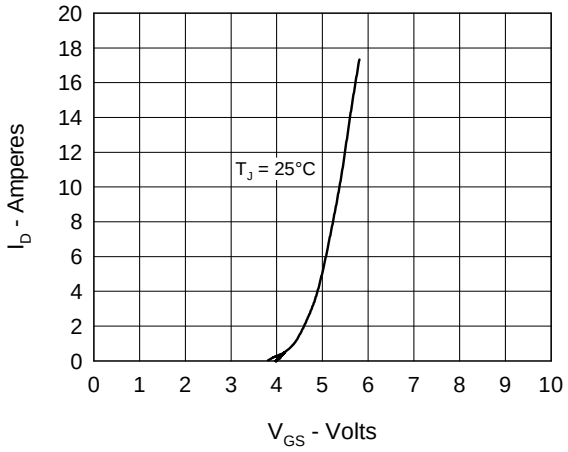


Fig. 3. $R_{DS(on)}$ vs. Drain Current

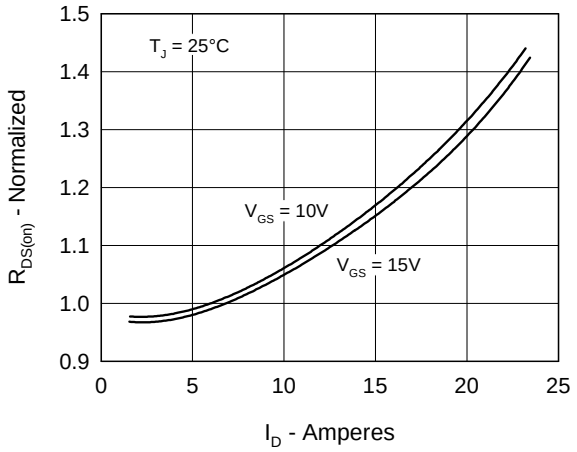


Fig. 4. Temperature Dependence of Drain to Source Resistance

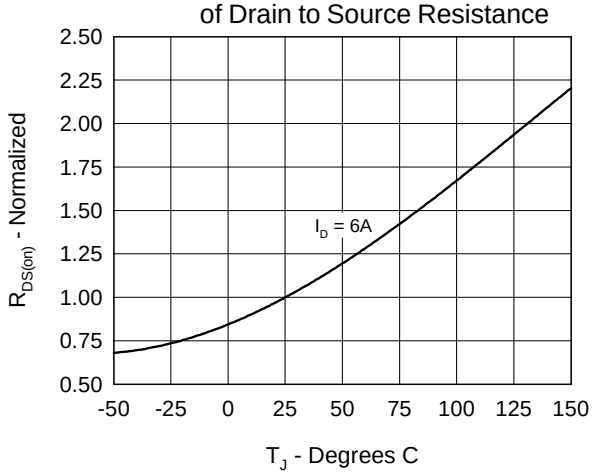


Fig. 5. Drain Current vs. Case Temperature

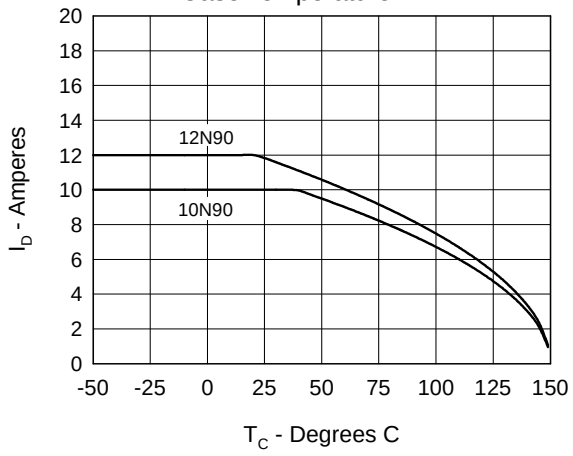
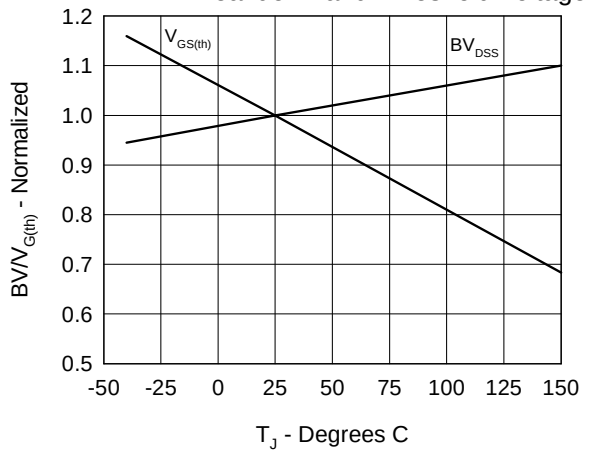


Fig. 6. Temperature Dependence of Breakdown and Threshold Voltage



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Fig.7. Gate Charge Characteristic Curve

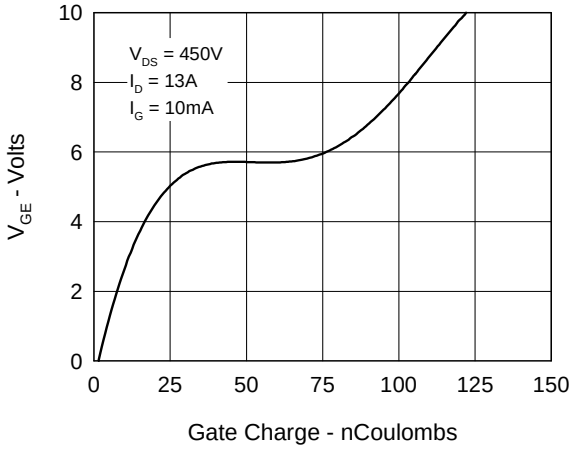


Fig.8. Capacitance Curves

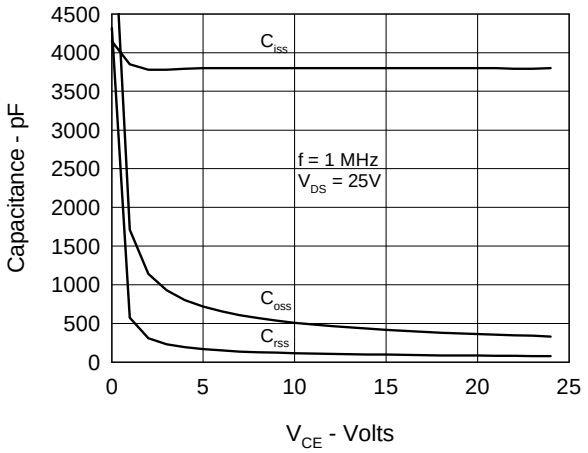


Fig.9. Source Current vs. Source to Drain Voltage

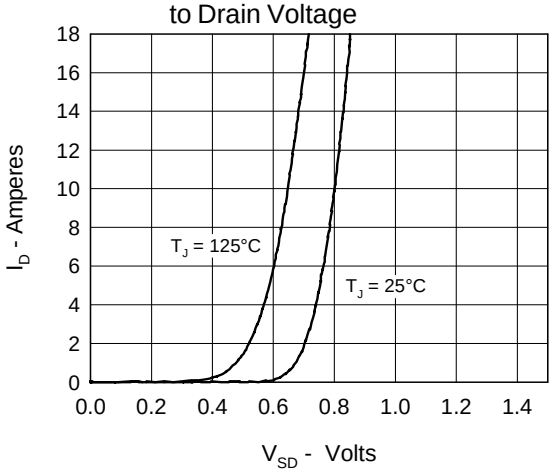
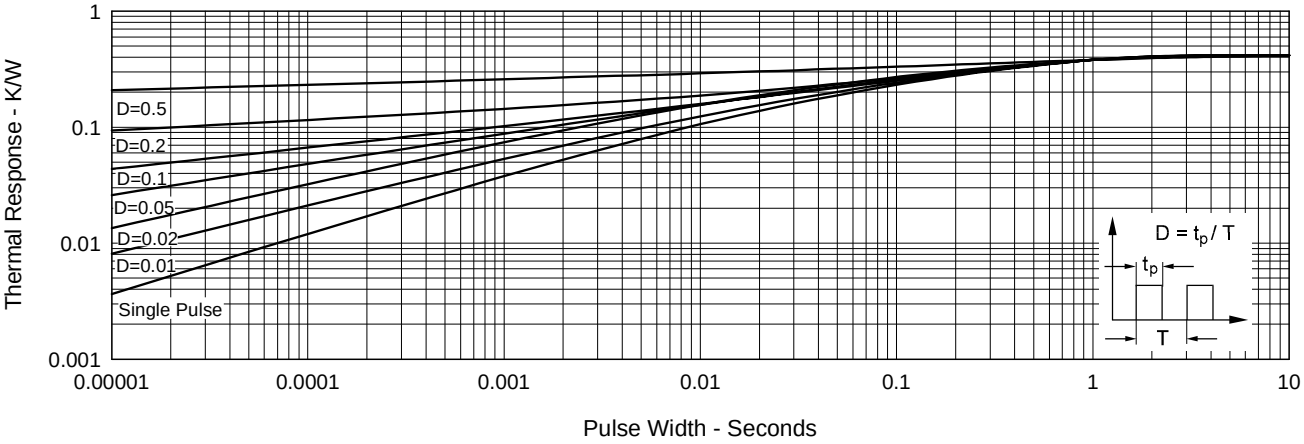


Fig.10. Transient Thermal Impedance



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